

$$\begin{aligned} \hbar &:= 1.05459 \cdot 10^{-34} \text{ J}\cdot\text{s} & q &:= 1.6 \cdot 10^{-19} \text{ C} & m_0 &:= 9.11 \cdot 10^{-31} \text{ kg} & \text{eV} &:= 1.6 \cdot 10^{-19} \text{ J} \\ n_r &:= 3.1 & \epsilon_0 &:= 8.854 \cdot 10^{-12} \text{ F}\cdot\text{m}^{-1} & \text{meV} &:= 0.001 \text{ eV} \\ E_g &:= 1 \text{ eV} & E_v &:= 0 & E_c &:= E_v + E_g & \omega &:= \frac{E_g}{\hbar} \\ k_B &:= 1.38 \cdot 10^{-23} \text{ J}\cdot\text{K}^{-1} & T &:= 300 \text{ K} & k_B \cdot T &= 0.026 \text{ eV} \end{aligned}$$

1(a) $T = 0 \text{ K}$

$$m_e := 0.5 \cdot m_0 \quad m_h := 0.5 \cdot m_0 \quad m_r := \frac{m_e \cdot m_h}{m_e + m_h} \quad \frac{m_r}{m_0} = 0.25$$

$$L_z := 10 \text{ nm}$$

$$C_0 := \frac{\pi \cdot q^2}{m_0^2 \cdot \omega \cdot \epsilon_0 \cdot c \cdot n_r} \quad C_0 = 7.762 \times 10^9 \frac{\text{m}^2}{\text{kg}} \quad E_p := 24 \text{ eV} \quad \frac{m_0}{6} \cdot E_p = 5.83 \times 10^{-49} \cdot \text{kg}\cdot\text{J}$$

$$\rho_r(h\nu) := \text{if} \left(h\nu \geq E_g, \frac{m_r}{\pi \hbar^2 \cdot L_z}, 0 \right)$$

$$\alpha_0(h\nu) := C_0 \cdot \frac{m_0}{6} \cdot E_p \cdot \rho_r(h\nu)$$

At $T = 0 \text{ K}$, the gain is flat from E_g to ΔF for quantum well gain media.

$$\alpha_0(1.052 \text{ eV}) = 2.95 \times 10^4 \cdot \text{cm}^{-1}$$

(b) $\text{Gain spectral width} = \Delta h\nu = \Delta F - E_g = 52 \text{ meV}$ (c) Electron quasi-Fermi level is $1/2$ of $\Delta F - E_g = 26 \text{ meV}$

$$N := \frac{m_e}{\pi \hbar^2 \cdot L_z} \cdot 26 \text{ meV} \quad N = 5.423 \times 10^{18} \cdot \text{cm}^{-3}$$

$$P := N \quad P = 5.423 \times 10^{18} \cdot \text{cm}^{-3}$$

(d) The slope of Fermi inversion function at ΔF is $1/4kT$
Gain peak at 300 K now appear at band edge, E_g

$$T := 300 \text{ K} \quad \Delta F := E_g + 52 \text{ meV}$$

$$f_g(h\nu) := \frac{-1}{4k_B \cdot T} \cdot (h\nu - \Delta F)$$

$$g(h\nu) := C_0 \cdot \frac{m_0}{6} \cdot E_p \cdot \rho_r(h\nu) \cdot f_g(h\nu)$$

$$g_{\text{peak}} := g(E_g)$$

$$g_{\text{peak}} = 1.482 \times 10^4 \cdot \text{cm}^{-1}$$

(e) Peak wavelength occurs at the effective bandgap, $h\nu = E_g = 1 \text{ eV} = \boxed{1.24 \text{ } \mu\text{m}}$

(f) Like Fermi inversion factor, the Fermi-Dirac distribution can be approximated by a line with slope of $1/4kT$

$$F_c := E_c + \frac{1}{2}(\Delta F - E_g) \quad F_c = 1.026 \cdot \text{eV}$$

Taylor expansion of Fermi-Dirac distribution around F_c :

$$F_e(E) := \frac{1}{2} - \frac{1}{4k_B \cdot T} \cdot (E - F_c)$$

$$F_e(E_g) = 0.751$$

$$N := \frac{m_e}{\pi \hbar^2 \cdot L_z} \cdot \frac{1}{2} \cdot F_e(E_g) \cdot (F_c - E_g) \quad N = 2.037 \times 10^{18} \cdot \text{cm}^{-3}$$

Hole concentration is the same as electron concentration.

2.(a)

$$g(\hbar\omega) = C_0 \left| \hat{e} \cdot \vec{P}_{cv} \right|^2 \rho_r(\hbar\omega) f_g(\hbar\omega)$$

At $T = 0 \text{ K}$, gain peak occurs at $\hbar\omega = \Delta F$

$$g_{\text{peak}} = C_0 \left| \hat{e} \cdot \vec{P}_{cv} \right|^2 \frac{1}{2\pi^2} \left(\frac{2m_r^*}{\hbar^2} \right)^{3/2} \sqrt{\Delta F - E_g}$$

$$\frac{g_{\text{peak},A}}{g_{\text{peak},B}} = \left(\frac{m_{r,A}^*}{m_{r,B}^*} \right)^{3/2}$$

$$m_{rA} := \frac{0.1 \cdot 0.1}{0.1 + 0.1} \cdot m_0$$

$$m_{rB} := \frac{0.1 \cdot 1}{0.1 + 1} \cdot m_0$$

$$\text{Peak_gain_ratio} := \left(\frac{m_{rA}}{m_{rB}} \right)^{1.5}$$

$$\text{Peak_gain_ratio} = 0.408$$

(b) At room temperature, the Fermi inversion factor at gain peak is < 1 . However, because the gain peak photon energy is the same for Semiconductor A and B, the Fermi inversion factors cancel out. So the peak gain ratio remains the same.

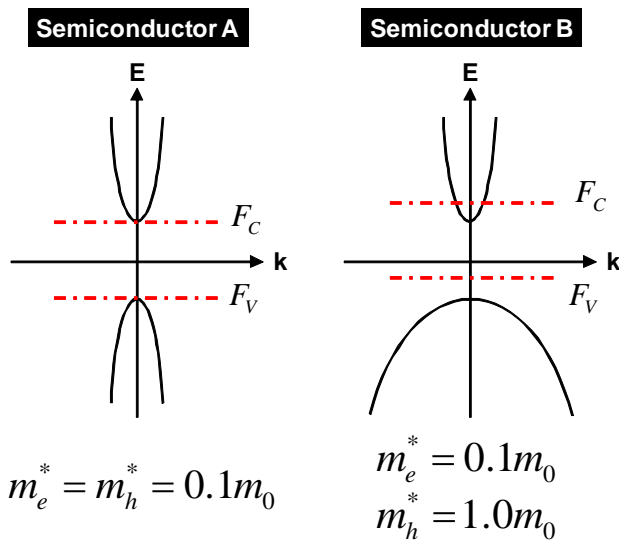
(c)

$$n = 2 \left(\frac{\pi m_e^* k_B T}{2\pi^2 \hbar^2} \right)^{3/2} 4 \left(\frac{F_n - E_C}{k_B T} \right)^{3/2}$$

$$n = \frac{8}{3\sqrt{\pi}} \left(\frac{\pi m_e^* (F_n - E_C)}{2\pi^2 \hbar^2} \right)^{3/2}$$

$$\frac{n_A}{n_B} = \left(\frac{m_{e,A}^* (F_n - E_C)_A}{m_{e,B}^* (F_n - E_C)_B} \right)^{3/2} = \left(\frac{(F_n - E_C)_A}{(F_n - E_C)_B} \right)^{3/2} = \left(\frac{\frac{\Delta F}{2}}{(F_n - E_C)_B} \right)^{3/2} < 1$$

(d) Semiconductor A will have lower transparency carrier concentration. Since it has symmetric effective masses, F_c is exactly at E_c for Semiconductor A. In Semiconductor B, F_c will lie above E_c because of larger hole effective mass. As a result, it has higher electron concentration.



3. (a)

$$h\nu := \frac{1.24 \text{ eV} \cdot \mu\text{m}}{5 \mu\text{m}} \quad h\nu = 0.248 \cdot \text{eV} \quad \underline{m_e := 0.1 m_0} \quad \underline{m_h := 0.5 m_0}$$

$$E1_n(Lz) := \frac{\hbar^2}{2 \cdot m_e} \cdot \left(\frac{\pi}{Lz}\right)^2 \quad E1_p(Lz) := \frac{\hbar^2}{2 \cdot m_h} \cdot \left(\frac{\pi}{Lz}\right)^2$$

$Lz := 10 \text{ nm}$ (initial guess value)

Given

$$E1_n(Lz) = \frac{h\nu}{3} \quad Lz_n := \text{Find}(Lz) \quad \boxed{Lz_n = 6.749 \cdot \text{nm}}$$

$$E1_p(Lz) = \frac{h\nu}{3} \quad Lz_p := \text{Find}(Lz) \quad \boxed{Lz_p = 3.018 \cdot \text{nm}}$$

(b)

$$\alpha(\hbar\omega) = \frac{\pi\omega}{n_r c \varepsilon_0} g(E_{e1}^{e2}) |\mu_{21}|^2 \frac{m_e^*}{\pi \hbar^2 L_z} E_{e1}^{e2}$$

$$= \frac{\pi\omega}{n_r c \varepsilon_0} g(E_{e1}^{e2}) \left(-\frac{16}{9\pi^2} e L_z\right)^2 \frac{m_e^*}{\pi \hbar^2 L_z} E_{e1}^{e2}$$

$$\frac{\alpha_{\max,N}}{\alpha_{\max,P}} = \frac{L_{z,N} m_e^*}{L_{z,P} m_h^*}$$

$$\alpha_ratio := \frac{Lz_n \cdot m_e}{Lz_p \cdot m_h} \quad \boxed{\alpha_ratio = 0.447}$$

(c)

$$N_{\max} = \frac{m_e^*}{\pi \hbar^2 L_{z,N}} \Delta E$$

$$P_{\max} = \frac{m_h^*}{\pi \hbar^2 L_{z,P}} \Delta E$$

$$\frac{N_{\max}}{P_{\max}} = \frac{\frac{m_e^*}{L_{z,N}}}{\frac{m_h^*}{L_{z,P}}}$$

$$N_P_ratio := \frac{m_e \cdot Lz_p}{m_h \cdot Lz_n} \quad \boxed{N_P_ratio = 0.089}$$